

Corrigendum

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HORIZONTAL CURRENT BIPOLAR TRANSISTOR (HCBT) – A LOW-COST, HIGH-PERFORMANCE FLEXIBLE BICMOS TECHNOLOGY FOR RF COMMUNICATION APPLICATIONS.

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The Editor-in-Chief has been informed that in the article Tomislav Suligoj, Marko Koričić, Josip Žilak, Hidenori Mochizuki, So-Ichi Morita, Katsumi Shinomura, Hisaya Imai. Horizontal Current Bipolar Transistor (HCBT) – A Low-Cost, High-Performance Flexible BICMOS Technology for RF Communication Applications. *Facta Universitatis, Series: Electronics and Energetics*, Vol. 28, No 4, 2015, pp. 507-525. DOI: 10.2298/FUEE1504507S Fig. 15 with its legend has been omitted in published version of the paper. After further discussion with the corresponding author, Editor-in-Chief has decided to publish a corrigendum for this article, providing the figure and legend of Fig. 15.

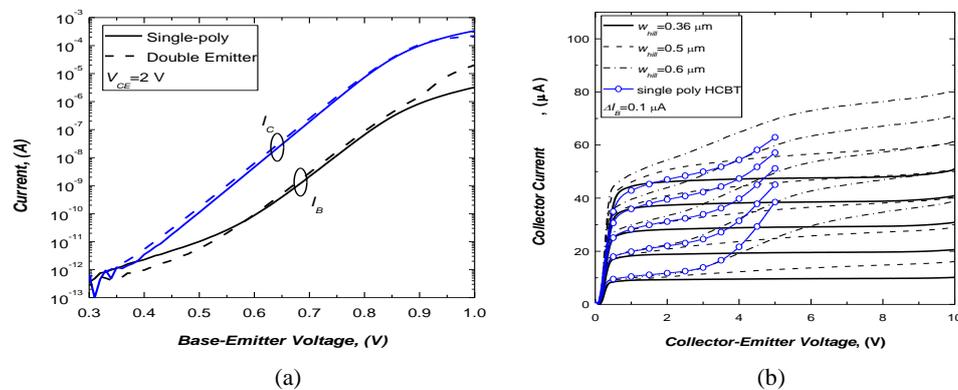


Fig. 15 Measured DC characteristics of double-emitter (DE) HCBT: (a) Comparison between the Gummel characteristics of DE HCBT with n-hill width $w_{hill}=0.36 \mu\text{m}$ (b) Output characteristics of DE HCBTs with different n-hill widths (w_{hill}). Single polysilicon region HCBT is added for the reference.

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